

Part Number

Customer

| Category      | Parameter | Specification                   | Measurement Method  |  |
|---------------|-----------|---------------------------------|---|--|
| OverallWafer  | 1.0       | Diameter                        | 100.00 +/- 0.50 mm  |  |
|               | 2.0       | Primary Flat Orientation        | {110} +/- 1 degree  | Wafer Vendor                               |
|               | 3.0       | Primary Flat Length             | 32.50 +/- 2.50 mm   | Wafer Vendor                               |
|               | 4.0       | Secondary Flat Orientation      | none / semi std   | wafer vendor                               |
|               | 5.0       | Overall Thickness               | 525.00 +/- 25.00 $\mu$ m  | ADE, 100%                                  |
|               | 6.0       | Total Thickness Variation (TTV) | <10.00 $\mu$ m  | ADE, 100% measurement                      |
|               | 7.0       | Bow                             | <40.00 $\mu$ m  | ADE to ASTM F534, 20%                      |
|               | 8.0       | Warp                            | <40.00 $\mu$ m  | ADE to ASTM F657, 20%                      |
|               | 9.0       | Edge Chips                      | 0   | Bright Light, 100% (note 2)                |
|               | 10.0      | Edge Exclusion                  | 5mm   |  |
| HandleSilicon | 11.0      | Handle Growth Method            | CZ  | Wafer Vendor                               |
|               | 12.0      | Handle Orientation              | {100} +/- 1 degree  | Wafer Vendor                               |
|               | 13.0      | Handle Thickness                | 525.00 +/- 25.00 $\mu$ m  | ADE, 100%                                  |
|               | 14.0      | Handle Doping Type              | N   | Wafer Vendor                               |
|               | 15.0      | Handle Dopant                   | Phosphorous   | Wafer Vendor                               |
|               | 16.0      | Handle Resistivity              | 1 - 20 Ohmcm  | Wafer Vendor                               |
|               | 17.0      | Backside Finish                 | Polished with 3.8 $\mu$ m +/- 0.6 $\mu$ m oxide and lasermark, no polysilicon. Planarise after phosphorous deposition of poly | Wafer Vendor                               |
| DeviceSilicon | 18.0      | LPD Count                       | <30.00pcs   | @0.3 $\mu$ m, Tencor 6220 particle counter |
|               | 19.0      | Scratches                       | 0   | Bright Light, 100% (note 2)                |
|               | 20.0      | Haze                            | none  | Bright Light, 100% (note 2)                |
|               | 21.0      | Surface                         | front side prime polished (before oxide and poly deposition)  | Guaranteed by process                      |
|               | 23.0      | Device Field Oxidation          | 40,000.00 +/- 2,000.00 A  | Nanospec 4%, 5pt                           |
| Trench        | 24.0      | Poly refill thickness           | 20000A +/- 1000A, doped as per the schedule in notes. Sheet resistance of poly <2.8 Ohms per sq                               | 4 pt probe 100%                            |

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|                  |                   |   |
|------------------|-------------------|---|
| Shipping Details | Wafer per box :   | Max 25  |
|                  | Packaging :       | Taped Polypropylene Wafer Box<br>Empak, Ultrapak, 100.00mm<br>Antistatic Double Bagging |
|                  | Lot Shipment Data | Device Thickness<br>Bow / Warp Data<br>Handle and SOI Thickness                         |



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information